A RESISTIVE MEMORY ARRANGEMENT AND A METHOD OF FORMING THE SAME

ABSTRACT

According to embodiments of the present invention, a resistive memory arrangement is provided. The resistive memory arrangement includes a nanowire, and a resistive memory cell including a resistive layer including a resistive changing material, wherein at least a section of the resistive layer is arranged covering at least a portion of a surface of the nanowire, and a conductive layer arranged on at least a part of the resistive layer. According to further embodiments of the present invention, a method of forming a resistive memory arrangement is also provided.

Figure 3A